

















6-Pin DIP Zero-Cross **Optoisolators Triac Driver Output** (600 Volts Peak)

The MOC3061, MOC3062 and MOC3063 devices consist of gallium arsenide infrared emitting diodes optically coupled to monolithic silicon detectors performing the functions of Zero Voltage Crossing bilateral triac drivers.

They are designed for use with a triac in the interface of logic systems to equipment powered from 115/240 Vac lines, such as solid-state relays, industrial controls, motors, solenoids and consumer appliances, etc.

- Simplifies Logic Control of 115/240 Vac Power
- Zero Voltage Crossing
- dv/dt of 1500 V/μs Typical, 600 V/μs Guaranteed
- To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.

Recommended for 115/240 Vac(rms) Applications:

- Solenoid/Valve Controls
- **Lighting Controls**
- Static Power Switches
- **AC Motor Drives**

- Temperature Controls
- E.M. Contactors
- AC Motor Starters
- · Solid State Relays

MAXIMUM RATINGS

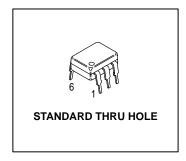
Rating	Symbol	Value	Unit
INFRARED EMITTING DIODE			
Reverse Voltage	V _R	6	Volts
Forward Current — Continuous	lF	60	mA
Total Power Dissipation @ T _A = 25°C Negligible Power in Output Driver Derate above 25°C	PD	120 1.41	mW mW/°C
OUTPUT DRIVER			

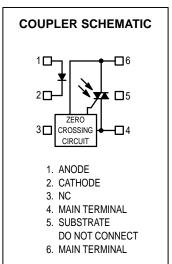
Off-State Output Terminal Voltage 600 Volts **VDRM** Peak Repetitive Surge Current 1 Α ITSM $(PW = 100 \mu s, 120 pps)$ Total Power Dissipation @ T_A = 25°C P_{D} 150 mW Derate above 25°C 1.76 mW/°C

TOTAL DEVICE

Isolation Surge Voltage ⁽¹⁾ (Peak ac Voltage, 60 Hz, 1 Second Duration)	VISO	7500	Vac(pk)
Total Power Dissipation @ T _A = 25°C Derate above 25°C	PD	250 2.94	mW mW/°C
Junction Temperature Range	TJ	-40 to +100	°C
Ambient Operating Temperature Range	TA	-40 to +85	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C
Soldering Temperature (10 s)	TL	260	°C

MOC3061 **MOC3062 MOC3063**





^{1.} Isolation surge voltage, $V_{\mbox{\scriptsize ISO}}$, is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
INPUT LED					
Reverse Leakage Current (V _R = 6 V)	l _R	_	0.05	100	μА
Forward Voltage (I _F = 30 mA)	VF	_	1.3	1.5	Volts
OUTPUT DETECTOR (I _F = 0)					
Leakage with LED Off, Either Direction (Rated V _{DRM} ⁽¹⁾)	I _{DRM1}	_	60	500	nA
Critical Rate of Rise of Off–State Voltage ⁽³⁾	dv/dt	600	1500	_	V/μs
COUPLED					
LED Trigger Current, Current Required to Latch Output (Main Terminal Voltage = 3 V ⁽²⁾) MOC3061 MOC3062 MOC3063	lFT			15 10 5	mA
Peak On–State Voltage, Either Direction (I _{TM} = 100 mA, I _F = Rated I _{FT})	V _{TM}	_	1.8	3	Volts
Holding Current, Either Direction	lн	_	250	_	μΑ
Inhibit Voltage (MT1–MT2 Voltage above which device will not trigger.) (IF = Rated IFT)	VINH	_	5	20	Volts
Leakage in Inhibited State (IF = Rated IFT, Rated VDRM, Off State)	I _{DRM2}	_	_	500	μА
Isolation Voltage (f = 60 Hz, t = 1 sec)	VISO	7500	_	_	Vac(pk)

- 1. Test voltage must be applied within dv/dt rating.
- 2. All devices are guaranteed to trigger at an I_F value less than or equal to max I_{FT}. Therefore, recommended operating I_F lies between max I_{FT} (15 mA for MOC3061, 10 mA for MOC3062, 5 mA for MOC3063) and absolute max I_F (60 mA).
- 3. This is static dv/dt. See Figure 7 for test circuit. Commutating dv/dt is a function of the load–driving thyristor(s) only.

TYPICAL CHARACTERISTICS

T_A = 25°C

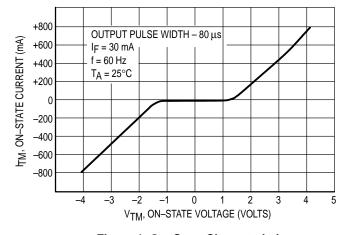


Figure 1. On-State Characteristics

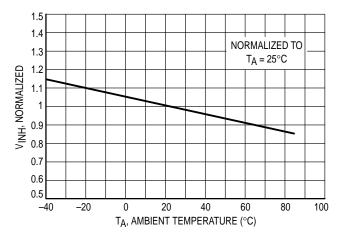


Figure 2. Inhibit Voltage versus Temperature





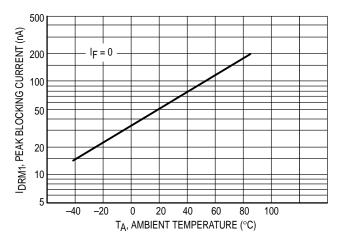


Figure 3. Leakage with LED Off versus Temperature

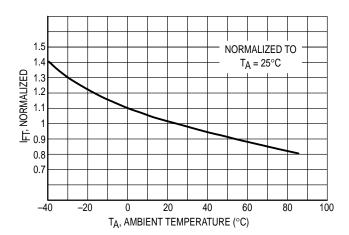
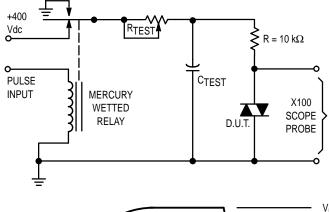
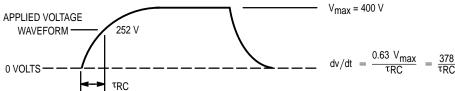


Figure 5. Trigger Current versus Temperature





1.5 1.4 1.3 IF = RATED IFT IDRM2, NORMALIZED 1.2 1.1 0.9 0.8 0.7 0.6 60 80 -20 40 TA, AMBIENT TEMPERATURE (°C)

Figure 4. IDRM2, Leakage in Inhibit State versus Temperature

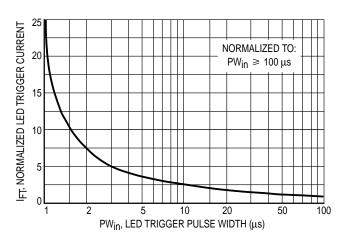


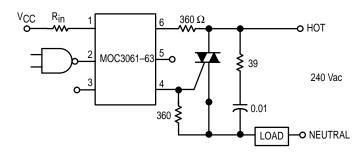
Figure 6. LED Current Required to Trigger versus LED Pulse Width

- 1. The mercury wetted relay provides a high speed repeated pulse to the D.U.T.
- 100x scope probes are used, to allow high speeds and voltages.
- 3. The worst–case condition for static dv/dt is established by triggering the D.U.T. with a normal LED input current, then removing the current. The variable RTESTallows the dv/dt to be gradually increased until the D.U.T. continues to trigger in response to the applied voltage pulse, even after the LED current has been removed. The dv/dt is then decreased until the D.U.T. stops triggering. TRC is measured at this point and recorded.

Figure 7. Static dv/dt Test Circuit



MOC3061, MOC3062, MOC3063



Typical circuit for use when hot line switching is required. In this circuit the "hot" side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.

 $R_{\mbox{\scriptsize in}}$ is calculated so that IF is equal to the rated IFT of the part, 15 mA for the MOC3061, 10 mA for the MOC3062, and 5 mA for the MOC3063. The 39 ohm resistor and 0.01 μF capacitor are for snubbing of the triac and may or may not be necessary depending upon the particular triac and load used.

Figure 8. Hot-Line Switching Application Circuit

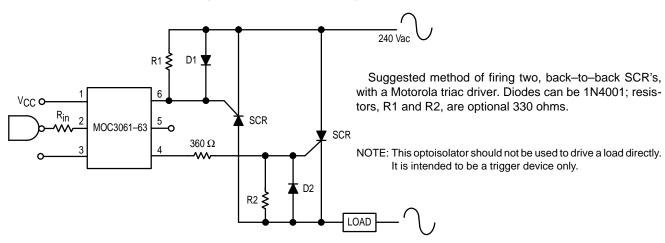
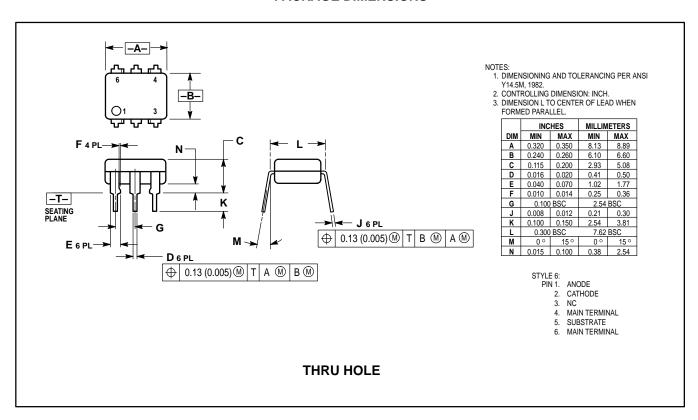


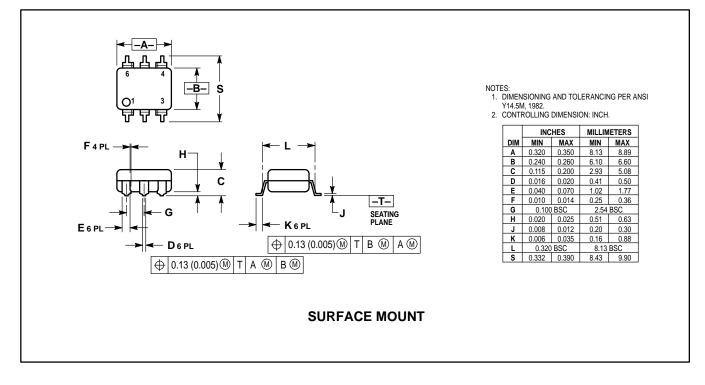
Figure 9. Inverse-Parallel SCR Driver Circuit





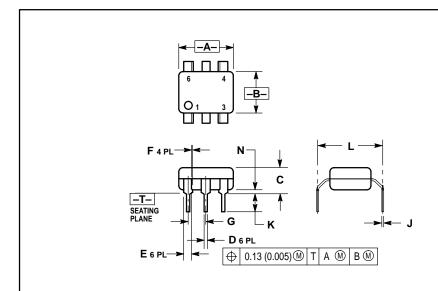
PACKAGE DIMENSIONS











- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.320	0.350	8.13	8.89	
В	0.240	0.260	6.10	6.60	
С	0.115	0.200	2.93	5.08	
D	0.016	0.020	0.41	0.50	
Е	0.040	0.070	1.02	1.77	
F	0.010	0.014	0.25	0.36	
G	0.100 BSC		2.54 BSC		
J	0.008	0.012	0.21	0.30	
K	0.100	0.150	2.54	3.81	
L	0.400	0.425	10.16	10.80	
N	0.015	0.040	0.38	1.02	

0.4" LEAD SPACING



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